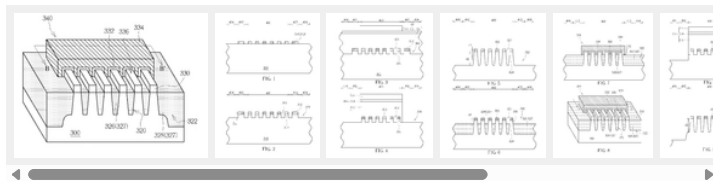


Non-planar transistor

Abstract

A method of forming a fin structure is provided. First, a substrate is provided, wherein a first region, a second region encompassing the first region, and a third region encompassing the second region are defined on the substrate. Then, a plurality of first trenches having a first depth are formed in the first region and the second region, wherein each two first trenches defines a first fin structure. The first fin structure in the second region is removed. Lastly, the first trenches are deepened to form a plurality of second trenches having a second depth, wherein each two second trenches define a second fin structure. The present invention further provides a structure of a non-planar transistor.

Images (8)



Classifications

H01L29/7851

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Claims (6)

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What is claimed is:

1. A non-planar transistor, comprising:

a substrate having an active region and an isolation region, wherein the isolation region encompasses the active region;

a plurality of shallow trenches disposed in the substrate in the active region, wherein a portion of the substrate between each two shallow trenches is defined as a protruding structure, and the protruding structure has an upper portion having a substantially vertical sidewall and a lower portion having a tilted sidewall;

a deep trench disposed in the substrate in the isolation region, wherein the deep trench is deeper than the shallow trenches and has a shoulder portion;

an insulation layer disposed in the shallow trenches and the deep trench, wherein an upper surface of the insulation layer in the shallow trenches is level with that in the deep trench;

a portion of the protruding structure that protrudes over the insulation layer defined as a fin structure;

a conductive layer disposed on the fin structure; and

a gate dielectric layer disposed between the fin structure and the conductive layer.

2. The non-planar transistor according to claim 1, wherein the upper portion has a height between 200 and 400 angstroms.

3. The non-planar transistor according to claim 1, wherein the lower portion has a height between 1000 and 2000 angstroms.

4. The non-planar transistor according to claim 1, wherein the upper surface of the insulation layer is higher than the lower portion.

5. The non-planar transistor according to claim 1, wherein the shoulder portion includes a round corner.

6. The non-planar transistor according to claim 1, wherein each of the fin structures has a same size.

US9117909B2

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Current Assignee: Marlin Semiconductor Ltd

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Application US14/470,957 events

• First worldwide family litigation filed

2014-08-28 • Application filed by United Microelectronics Corp

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2014-12-18 • Publication of US20140367798A1

2015-08-25 • Application granted

2015-08-25 • Publication of US9117909B2

Status • Active

2033-04-16 • Anticipated expiration

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Description

CROSS REFERENCE TO RELATED APPLICATIONS

This application is a Divisional of application Ser. No. 13/863,393 filed Apr. 16, 2013, and included herein by reference.

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention is related to a method of forming a fin structure of a non-planar transistor, and more particularly, to a method of forming at least a fin structure having nearly identical critical dimension (CD).

2. Description of the Prior Art

In recent years, as various kinds of consumer electronic products are being constantly modified towards increased miniaturization, the size of semiconductor components are modified to be reduced accordingly, in order to meet high integration, high performance, low power consumption, and the demands of products.

However, with the increasing miniaturization of electronic products, current planar FETs no longer meet the requirements of the products. Thus, non-planar FETs such as Fin-shaped FETs (Fin-FET) have been developed, which includes a three-dimensional channel structure. The manufacturing processes of Fin-FET devices can be integrated into traditional logic device processes, and thus are more compatible. In addition, since the three-dimensional structure of the Fin-FET increases the overlapping area between the gate and the substrate, the channel region is controlled more effectively. This therefore reduces drain-induced barrier lowering (DIBL) effect and short channel effect. Moreover, the channel region is longer for the same gate length. Therefore, the current between the source and the drain is increased. In recent years, the development of the Fin-FETs is still aiming to be used in devices with smaller scales.

However, some issues, such as poor CD uniformity of the fin structures of Fin-FETs, are still problems that should be overcome.

SUMMARY OF THE INVENTION

It is one objective of the present invention to provide a method of forming at least a fin structure having nearly identical CD.

According to one embodiment, a method of forming a fin structure is provided. First, a substrate is provided, wherein a first region, a second region encompassing the first region, and a third region encompassing the second region are defined on the substrate. Then, a plurality of first trenches having a first depth are formed in the first region and the second region, wherein each two first trenches defines a first fin structure. The first fin structure in the second region is removed. Lastly, the first trenches are deepened to form a plurality of second trenches having a second depth, wherein each two second trenches define a second fin structure.

According to another embodiment of the present invention, a non-planar transistor is provided. The non-planar transistor comprises a substrate, a plurality of second trenches, a sixth trench, an insulation layer, a conductive layer and a gate dielectric layer. The substrate has an active region and an isolation region, wherein the isolation region encompasses the active region. The second trenches are disposed in the substrate in active region, wherein a portion of the substrate between each two second trenches is defined as a second fin structure. The sixth trench is disposed in the substrate in the isolation region, wherein the sixth trench is deeper than the second trench. An insulation layer is disposed in the second trench and the sixth trench, wherein the insulation layer in the second trench is level with that in the sixth trench. A portion of the second fin structure that protrudes over the insulation layer is defined as a fin structure. The conductive layer is disposed on the fin structure. The gate dielectric layer is disposed between the fin structure and the conductive layer.

By using the method set forth in the present invention, the CD of the fin structures can be uniform and the quality of the devices can be improved.

These and other objectives of the present invention will no doubt become obvious to those of ordinary skill in the art after reading the following detailed description of the preferred embodiment that is illustrated in the various figures and drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 to FIG. 8 are schematic diagrams of the fabrication method of a non-planar transistor according to the first embodiment in the present invention.

FIG. 9 to FIG. 13 are schematic diagrams of the fabrication method of a non-planar transistor according to the second embodiment in the present invention.

DETAILED DESCRIPTION

To provide a better understanding of the present invention, preferred embodiments will be made in detail. The preferred embodiments of the present invention are illustrated in the accompanying drawings with numbered elements.

Please refer to FIG. 1 to FIG. 8, which are schematic diagrams of the fabrication method of a non-planar FET according to the first embodiment in the present invention. As shown in FIG. 1, a substrate **300** is provided. In one embodiment, the substrate **300** can be a silicon substrate, an epitaxial silicon substrate, a silicon germanium substrate or a silicon carbide substrate, but is not limited thereto. A first region **400**, a second region **402** and a third region **404** are defined on the substrate **300**. The second region **402** is disposed between the first region **400** and the third region **404** so that the second region **402** encompasses the first region **400**, and the third region **404** encompasses both the first region **400** and the second region **402**. A patterned mask layer **302** is formed on the substrate **300**. For example, a layer such as a silicon nitride (SiN) layer, a silicon oxynitride (SiON), silicon carbide (SiC) or an advanced pattern film (APF) provided by Applied Materials, is formed on the substrate **300** and a photo-etching-process (PEP) is performed to pattern the mask layer **302**. In another embodiment, the method of forming the patterned mask layer **302** can include other processes such as a sidewall image transferring (SIT) process. The mask layer **302** contains a plurality of patterns **304**, preferably stripe patterns that are parallel to each other in the first region **400** and the second region **402**. In one embodiment, the stripe patterns **304** are disposed only in the first region **400** and the second region **402**. As shown in FIG. 1, due to some manufacturing effects such as "dense-isolation effect" or "micro-loading effect", the width of the stripe pattern **304** in the second region **402** would be a little larger than those in the first region **400**.

As shown in FIG. 2, an etching process is performed by using the mask layer **302** as a mask to pattern the substrate **300**, thereby forming a plurality of first trenches **306** in the first region **400** and the second region **402**, and a third trench **308** in the third region **404**. By adjusting the etching recipe or the etching rate, the first trench **306** preferably has a substantial vertical sidewall. In one embodiment, each first trench **306** has a depth d1 (from bottom surface of the first trench **306** to a top surface of the substrate **300**) which is substantially between 200 and 400 angstroms, preferably 300 and 350 angstroms. Simultaneously, the portion of the substrate **300** between each of the two first trenches **306** becomes a first protruding structure **310** (in the present invention, "the protruding structure" can also be called "the fin structure" since the mask layer **302** has stripe patterns **304**).

Next, the first protruding structures **310** in the second region **402** are removed. As shown in FIG. 3 to FIG. 4, a photo-etching-process (PEP) using a tri-layer photoresist material **318** is used for example. In one embodiment, the tri-layer photoresist material **318** contains a photoresist layer **316**, an anti-reflection coating (ARC) **314** and an auxiliary mask layer **312**. In one embodiment, the photoresist layer **316** is a photoresist material suitable for light source having a wavelength of 193 nm. The ARC layer **314** includes a silicon-containing hard-mask bottom anti-reflection coating (SHB) layer and the auxiliary mask layer **312** includes an organic dielectric layer (ODL) provided by Shin-Etsu Chemical Co. Ltd., wherein the SHB layer is disposed directly under the photoresist layer to serve as a BARC and a mask layer, and the ODL layer is an organic underlayer, i.e., a hydrocarbon layer, which is used to serve as an auxiliary mask layer. As shown in FIG. 3, the photoresist layer **316** undergoes an exposure process and a development process to remove the photoresist layer **316** in the second region **402** and the third region **404**. Then, as shown in FIG. 4, at least one etching process is performed by using the patterned photoresist layer **316** as a mask to sequentially pattern the ARC layer **314**, the auxiliary mask layer **312**, and then remove the mask layer **302** and the first protruding structure **310** in the second region **402**. In the present embodiment, the etching process stops on the bottom surface of the third trench **308**, so the third trench **308** is still level with the first trenches **306**. Then, the tri-layer photoresist material **318** is stripped away. It is noted that besides using the tri-layer photoresist material **318**, the first protruding structure **310** in the second region **402** can be removed by other methods.

As shown in FIG. 5, an etching process is performed by using the patterned mask layer **302** as a mask to simultaneously deepen the first trenches **306** and the third trench **308**. Each first trench **306** in the first region **400** becomes a second trench **320**, the third trench **308** in the second region **402** and the third region **404** becomes a fourth trench **322**, and the first protruding structure **310** becomes a second protruding structure **324**. In one embodiment, each second trench **320** has a depth d2 which is substantially between 1200 angstroms and 2500 angstroms. In the present embodiment, the etching rate of forming the second trench **320** can be faster than that of forming the first trench **306**, so the lower portion of the second trench **320** may include tilted sidewalls.

As shown in FIG. 6, an insulation layer **327** is filled into the second trenches **320** and the fourth trench **322** to form a plurality of fin-STIs (shallow trench isolation) **326** in the second trench **320** and an STI **328** in the fourth trench **322**. For example, an insulation layer containing SiO₂ is deposited on the substrate **300** to completely fill the second trenches **320** and the fourth trench **322**. Then, a planarization process including an etching back step is performed to remove apart of the insulation layer **327** until exposing the second protruding structures **324**. Preferably, the insulation layer **327** in the second trench **320** has a thickness equal to or greater than the second depth d2. That is, the exposed portion of the second protruding structure **324** has a height h3, and the height h3 is substantially equal to the depth d1. In another embodiment, the height h3 can be smaller than the depth d1. Preferably, the portion of the second protruding structure **324** having the tilted sidewalls is not exposed. After forming the fin-STIs **326** and the STI **328**, a plurality of fin structures **330** are therefore formed. The fin structure **330** refers to the portion of the second protruding structures **324** that protrudes over the fin-STIs **326**. In other words, the fin structure **330** is the portion of the substrate **300** that is exposed and not covered by the fin-STI **326**, so the fin structure **330** has a height h3. In one embodiment, the mask layer **302** can be removed after forming the fin structures **330**. In another embodiment, the mask layer **302** can remain.

Then, please see FIG. 7 and FIG. 8, wherein FIG. 8 is a three dimensional view of the non-planar transistor and FIG. 7 is a cross-sectional view taken along line AA' in FIG. 8. A gate dielectric layer **332** is then formed to cover the fin structure **330**. The gate dielectric layer **332** can be, for example, a silicon layer or a high-k dielectric layer. Then, a gate layer **334** can be formed on the gate dielectric layer **332**. The gate layer **334** can include a variety of conductive materials, such as poly-silicon or metal. Next, after patterning the gate layer **334** to form the required gate structure, an ion implantation process is carried out to form the source/drain region **336** in the fin structure **330** as shown in FIG. 8. Through the above steps, a non-planar transistor **338** is completed. In the subsequent steps, an inter-layer dielectric (ILD) layer (not shown) can be further formed on the non-planar transistor **338**, and a plurality of contact holes (not shown) are formed therein to provide appropriate input/output pathway toward outer circuits.

By using the method in the present invention, some drawbacks in conventional arts can be avoided. For example, in conventional arts, only an etching process is performed by using a patterned mask layer to directly form the second protruding structures. However, due to the "dense-isolation effect" or "micro-loading effect", the width of the patterned mask layer in the second region will be larger (as shown FIG. 1), so the CD of the second protruding structures in the second region will become larger as well. Thus, the present invention includes the step of removing the first protruding structure **310** in the second region **402**, so as to keep the CD uniformity of the fin structure **330**.

Moreover, because the second protruding structures in conventional arts are formed by one single etching process, the second protruding structure in conventional arts is easy to have tapered sidewalls, especially those at the edge of the second protruding structures. Accordingly, the present invention uses two separated etching steps to form the second protruding structures **324**. Since the fin structure **330** only refers to the upper portion of the second protruding structures **324** which has vertical sidewalls, the CD of the fin structure **330** can be on target and meet the desired value.

It is another salient feature that the step of removing the first fin structures **310** in the second region **402** (FIG. 3 to FIG. 4) is performed between the etching step for forming the first trench **306** (FIG. 2) and the etching step for forming the second trench **320** (FIG. 6). If the removing step is performed before the two etching steps, the edge CD problem may still occur. If the removing step is performed after the two etching steps, the removing step cannot completely remove the fin structure since the trench is too deep and a silicon pillar structure will remain in the second region. Accordingly, the method in the present invention can ensure the CD of the fin structures and therefore upgrade the quality of the devices.

Please refer to FIG. 9 to FIG. 12, which are schematic diagrams of the fabrication method of a non-planar FET according to the second embodiment in the present invention. The previous steps in the second embodiment are similar to those in the first embodiment as in FIG. 1 to FIG. 3. After the steps in FIG. 1 to FIG. 3, please see FIG. 9. At least one etching process is performed by using the patterned photoresist layer **316** as a mask to sequentially pattern the ARC layer **314**, the auxiliary mask layer **312**, and then remove the mask layer **302** and the first protruding structure **310** in the second region **402**. In the present embodiment, the etching process further removes the substrate **300** in the second region **402** and the third region **404**, thereby forming a fifth trench **309** in the second region **402** and the third region **404**. The fifth trench **309** is not level with the first trench **306** but is deeper than the first trench **306**.

As shown in FIG. 10, an etching process is performed by using the patterned mask layer **302** as a mask to simultaneously deepen the first trenches **306** and the fifth trench **309**. In the first region **400**, each first trench **306** is deepened to form a second trench **320**. In the second region **402** and the third region, the fifth trench **309** is deepened to form a sixth trench **323**. It is understood that the sixth trench **323** is also deeper than the second trench **320**. Each first protruding structure **310** becomes a second protruding structure **324**. In one embodiment, each second trench **320** has a depth d2 which is substantially between 1200 angstroms and 2500 angstroms. The etching rate of forming the second trench **320** is faster than that of forming the first trench **306**, so the lower portion of the second trench **320** may include tilted sidewalls.

As shown in FIG. 11, an insulation layer **327** is filled into the second trenches **320** and the sixth trench **323** to form a plurality of fin-STIs **326** in the second trench **320** and an STI **328** in the sixth trench **322**. For example, an insulation layer containing SiO₂ is deposited on the substrate **300** to completely fill the second trenches **320** and the sixth trench **323**. Then, a planarization process including an etching back step is performed to remove a part of the insulation layer until exposing the second protruding structures **324**. In one embodiment, the second protruding structures **324** having a height h3 is exposed, wherein the height h3 is substantially equal to or smaller than the first depth d1. After forming the fin-STIs **326** and the STI **328**, a plurality of fin structures **330** are formed simultaneously. The fin structure **330** refers to each upper portion of the second protruding structures **324** that protrudes over the fin-STIs **326**. In other words, the fin structure **330** is the portion of the substrate **300** that is exposed and not covered by the fin-STI **326**. In one embodiment, the mask layer **302** can be removed after forming the fin structures **330**. In another embodiment, the mask layer **302** can remain.

Then, please see FIG. 12 and FIG. 13, wherein FIG. 13 is a three dimensional view of the non-planar transistor and FIG. 12 is a cross-sectional view taken along line BB' in FIG. 13. Gate dielectric layer 332 is formed to cover the fin structure 330. The gate dielectric layer 332 can be, for example, a silicon layer or a high-k dielectric layer. Then, a gate layer 334 can be formed on the gate dielectric layer 332. The gate layer 334 can include a variety of conductive materials, such as polysilicon or metal. Next, after patterning the gate layer 334 to form the required gate structure, anion implantation process is carried out to form the source/drain region 336 in the fin structure 330 as shown in FIG. 13. Through the above steps, the Fin-FET 340 structure in FIG. 13 can be provided.

As shown in FIG. 13, the non-planar transistor 340 includes a substrate 300, at least a fin structure 330, a gate dielectric layer 332, a gate 334, a source/drain region 336, at least a fin-STI 326 and an STI 323. An active region such as the first region 400 and an isolation region such as the third region 402 are defined on the substrate 300. At least a second trench 320 is disposed in the active region and a sixth trench 323 is disposed in the isolation region, wherein the sixth trench 323 is deeper than the second trench 320. An insulation layer 327 is disposed in the second trench 320 and the sixth trench 323, wherein the insulation layer 327 in the second trench 320 (fin-STI 326) is level with that in the sixth trench 323 (STI 328). The fin structure 330 is disposed between each of the two second trenches 320 and protrudes over the fin-STI 326. The gate 334 is disposed on the fin structure 330 and the gate dielectric layer 332 is disposed between the gate 334 and the fin structure 330. In one embodiment, the second protruding structure 324 has an upper portion 324 b having a substantial vertical sidewall, and a lower portion 324 a having a tilted sidewall. The upper portion 324 b has a height between 200 and 400 angstroms and the lower portion 324 a has a height between 1000 and 2000 angstroms. In one embodiment, an upper surface of the insulation layer 327 is level with the boundary between the upper portion 324 b and the lower portion 324 a. In another embodiment, the upper surface of the insulation layer 327 is higher than the lower portion 324 a.

Those skilled in the art will readily observe that numerous modifications and alterations of the device and method may be made while retaining the teachings of the invention. Accordingly, the above disclosure should be construed as limited only by the metes and bounds of the appended claims.

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CN107785315B	2020-05-08	Method of forming a semiconductor structure
CN110970299B	2024-01-26	Semiconductor devices and methods of forming the same
US11658076B2	2023-05-23	Semiconductor device and fabrication method thereof
TWI728966B	2021-06-01	Semiconductor device and method for fabricating the same
CN108630611A	2018-10-09	Semiconductor structure and forming method thereof
US10522619B2	2019-12-31	Three-dimensional transistor
CN109841507B	2020-11-27	Semiconductor device and method of forming the same
TWI703732B	2020-09-01	Method for fabricating semiconductor device
CN108122762B	2019-12-03	Semiconductor structure and forming method thereof
US9013024B2	2015-04-21	Semiconductor structure and process thereof
CN109427679B	2020-11-27	Semiconductor structure and method of forming the same
CN111276442A	2020-06-12	Semiconductor structure and method of forming the same
CN113745112B	2023-08-18	Method for forming semiconductor device
CN110858608B	2023-11-07	Semiconductor device and method of forming the same
CN109841527B	2022-03-18	Semiconductor structure and forming method thereof

Priority And Related Applications

Parent Applications (1)

Application	Priority date	Filing date	Relation	Title
US13/863,393	2013-04-16	2013-04-16	Division	Method of forming a FinFET structure

Priority Applications (1)

Application	Priority date	Filing date	Title
US14/470,957	2013-04-16	2014-08-28	Non-planar transistor

Applications Claiming Priority (2)

Application	Filing date	Title
US13/863,393	2013-04-16	Method of forming a FinFET structure
US14/470,957	2014-08-28	Non-planar transistor

Legal Events

Date	Code	Title	Description
2014-08-28	AS	Assignment	Owner name: UNITED MICROELECTRONICS CORP., TAIWAN Free format text: ASSIGNMENT OF ASSIGNORS INTEREST;ASSIGNORS:KUO, LUNG-EN;SU, PO-WEN;WENG, CHEN-YI;AND OTHERS;SIGNING DATES FROM 20130326 TO 20130408;REEL/FRAME:033625/0029
2015-08-05	STCF	Information on status: patent grant	Free format text: PATENTED CASE
2019-01-10	MAFP	Maintenance fee payment	Free format text: PAYMENT OF MAINTENANCE FEE, 4TH YEAR, LARGE ENTITY (ORIGINAL EVENT CODE: M1551); ENTITY STATUS OF PATENT OWNER: LARGE ENTITY Year of fee payment: 4
2021-07-26	AS	Assignment	Owner name: MARLIN SEMICONDUCTOR LIMITED, IRELAND Free format text: ASSIGNMENT OF ASSIGNORS INTEREST;ASSIGNOR:UNITED MICROELECTRONICS CORPORATION;REEL/FRAME:056991/0292 Effective date: 20210618
2023-02-15	MAFP	Maintenance fee payment	Free format text: PAYMENT OF MAINTENANCE FEE, 8TH YEAR, LARGE ENTITY (ORIGINAL EVENT CODE: M1552); ENTITY STATUS OF PATENT OWNER: LARGE ENTITY Year of fee payment: 8

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